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- (71) **Applicant (for all designated States except US):** MICRON TECHNOLOGY, INC. [US/US]; 8000 S Federal Way, Boise, ID 83716-9632 (US).
- (72) **Inventor; and**
- (75) **Inventor/Applicant (for US only):** LIU, Jun [CN/US]; 1033 S Dale Apt. #203, Boise, ID 83706 (US).
- (74) **Agents:** KERN, Jacob, T. et al.; Brooks, Cameron & Huebsch, PLLC, 1221 Nicollet Avenue, Suite 500, Minneapolis, MN 55403 (US).
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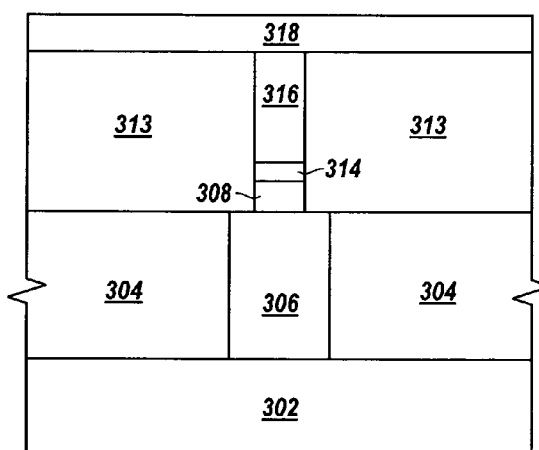
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(54) **Title:** PHASE CHANGE MEMORY STRUCTURES AND METHODS

**Fig. 3**

(57) **Abstract:** Methods, devices, and systems associated with phase change memory structures are described herein. One method of forming a phase change memory structure includes forming an insulator material on a first conductive element and on a dielectric material of a phase change memory cell, forming a heater self-aligned with the first conductive element, forming a phase change material on the heater and at least a portion of the insulator material formed on the dielectric material, and forming a second conductive element of the phase change memory cell on the phase change material.